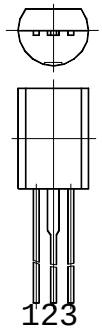
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SA966 TRANSISTOR (PNP)

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



FEATURE

Power dissipation

P_{CM}: 0.9 W(Tamb=25℃)

Collector current

I_{CM}: -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -30 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -1mA , I_E=0	-30		V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA , I_B=0	-30		V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -1mA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-2 V, I_C= -500mA	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -1.5 A, I_B= -0.03A		-2	V
Base-emitter voltage	V_{BE}	I_C= -500 mA, V_{CE}= -2V		-1	V
Transition frequency	f_T	V_{CE}= -2 V, I_C= -500mA	100		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320